

**Amendments to the Specification:**

Please replace paragraph [0038] with the following amended paragraph:

[0038] Next, as shown in Fig. 3D, using deposition, photolithography, and etching, a second metal layer formed on the gate insulating layer 46 forms the pattern of data lines 34a and 34b, the source electrodes S of the TFTs 38a and 38b, and the drain electrodes D of the TFTs 38a and 38b. Preferably, the second metal layer is Cr, Ta, Ti, Al or Mo. Accordingly, the first floating BM shielding layers 42A overlap across the ~~corresponding source electrodes S~~ extension portion of the first data line 34a, which is a part of the source electrodes S of the TFT 38b of an adjacent pixel area.